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WHAT IS CLAIMED IS:

1. A semiconductor device comprising:
 - a semiconductor substrate;
 - source/drain regions provided in the semiconductor substrate;
 - 5 a gate insulating film provided on a channel region between the source/drain regions;
 - a gate electrode provided on the gate insulating film;
- 10 a conductive layer of a metal silicide provided on the gate electrode and the source/drain regions;
- an insulating film containing carbon provided on the semiconductor substrate so as to be in contact with at least the conductive layer; and
- 15 an interlayer insulating film provided on the semiconductor substrate so as to cover the insulating film containing carbon.
2. The semiconductor device according to claim 1, wherein the insulating film containing carbon is mainly composed of a silicon nitride film.
3. The semiconductor device according to claim 2, wherein a content of the carbon is $1 \times 10^{20} \text{ cm}^{-3}$ or more.
4. The semiconductor device according to claim 1, wherein a metal of the metal silicide is nickel.
- 25 5. The semiconductor device according to claim 1, wherein a metal of the metal silicide is at least one